

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

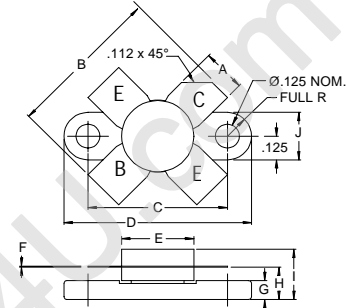
The **ASI SD1222-5** is a transistor designed primarily for 12.5 V AM Class-C amplifiers in the 118-136 MHz band and 28 V Class-C RF amplifiers in ground stations.

FEATURES:

- $P_G = 8.2$ dB min. at 5 W/30 MHz
- $IMD_3 = -30$ dBc max. at 20 W_(PEP)
- **Omnigold™** Metalization System
- Emitter Ballasting

MAXIMUM RATINGS

I_C	3.0 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	30 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	5.83 °C/W

PACKAGE STYLE .380 4L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200$ mA		35			V
BV_{CES}	$I_C = 200$ mA		65			V
BV_{EBO}	$I_E = 10$ mA		4.0			V
I_{CBO}	$V_{CB} = 30$ V				1.0	mA
I_{CES}	$V_{CE} = 30$ V	$T_A = 125$ °C			10	mA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 200$ mA	5.0			---
C_{ob}	$V_{CB} = 30$ V	$f = 1.0$ MHz			35	pF
G_p	$V_{CC} = 27$ V	$P_{OUT} = 20$ W			35	pF